

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a ferroelectric capacitor. In this method, a lower electrode is formed on a base at first. A ferroelectric film which includes a PZTN complex oxide including lead, zirconium, titanium, and niobium on the lower electrode is formed, and then an upper electrode is formed on the ferroelectric film. A protective film is then formed to cover the lower electrode, the ferroelectric film, and the upper electrode, and heat treatment for crystallizing the PZTN complex oxide is performed at least after forming the protective film.

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